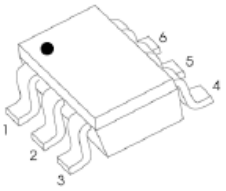
BC857BS

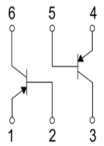
DUAL TRANSISTOR (PNP+PNP)

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: 3C





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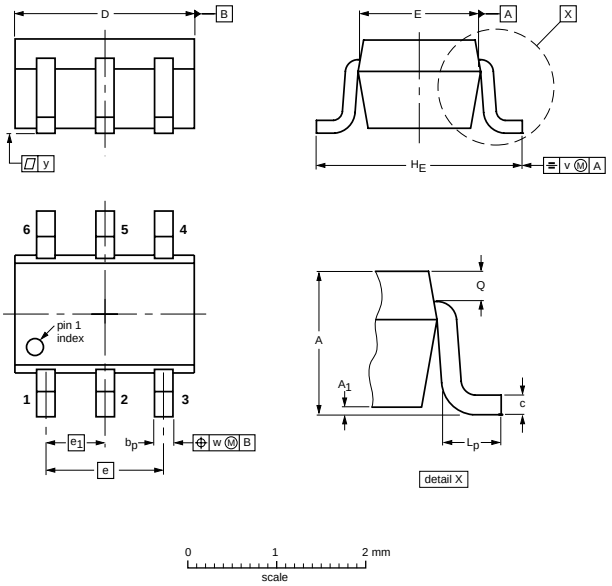

DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

MAXIMUM RATINGS(T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

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ELECTRICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-10μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-10mA,I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V,I_E=0			-15	nA
DC current gain	h_{FE}	V_{CE}=-5V,I_C=-2mA	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	I_C=-10mA,I_B=-0.5mA			-0.3	V
	$V_{CE(sat)(2)}$	I_C=-100mA,I_B=-5mA			-0.65	V
Base-emitter voltage	$V_{BE(1)}$	V_{CE}=-5V,I_C=-2mA	-0.6		-0.75	V
	$V_{BE(2)}$	V_{CE}=-5V,I_C=-10mA			-0.82	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-10mA,f=100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		3.5		pF
Noise figure	NF	V_{CE}=-5V,I_c=-0.2mA, f=1kHZ,Rs=2KΩ,BW=200Hz		2.5		dB

RATING AND CHARACTERISTIC CURVES (BC857BS)